FIGURES

Figure1. Example of 2D material integration with high-k

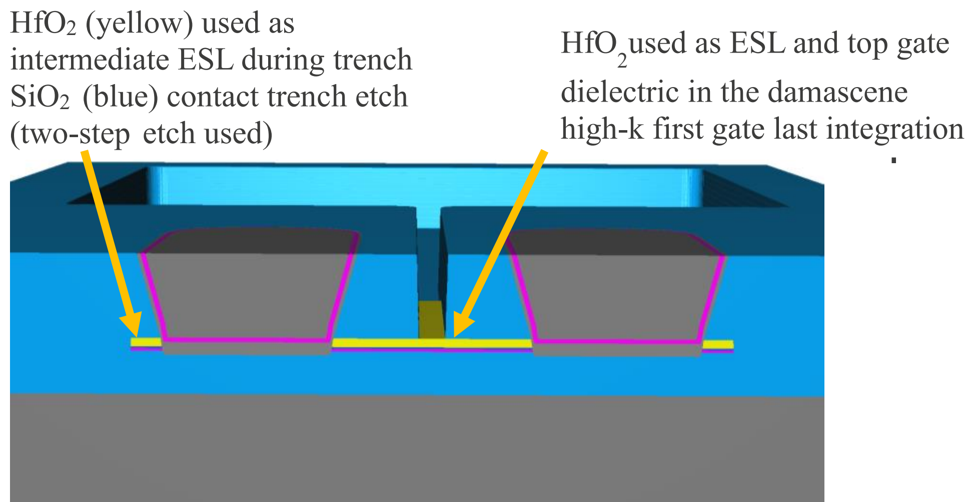
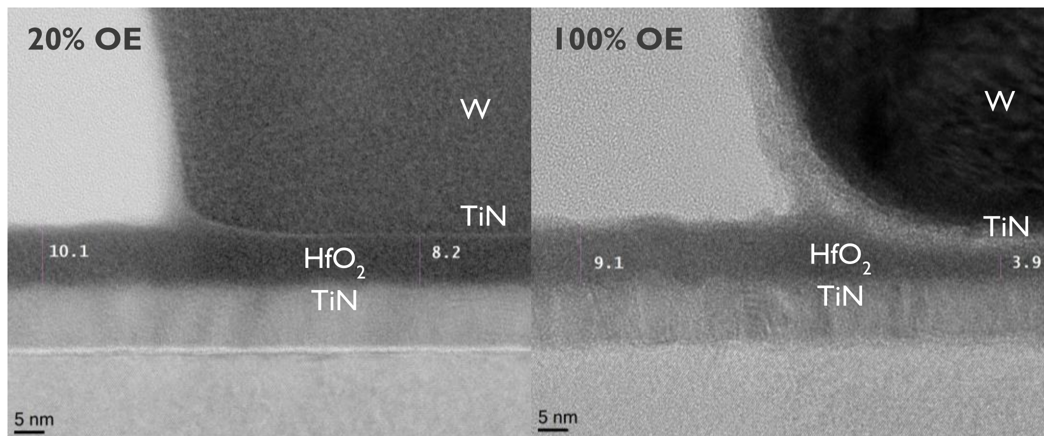


Figure 2. TEM images after SiO_2 etch and metallization a) CW; b) Q-ALE respectively.

a)



b)

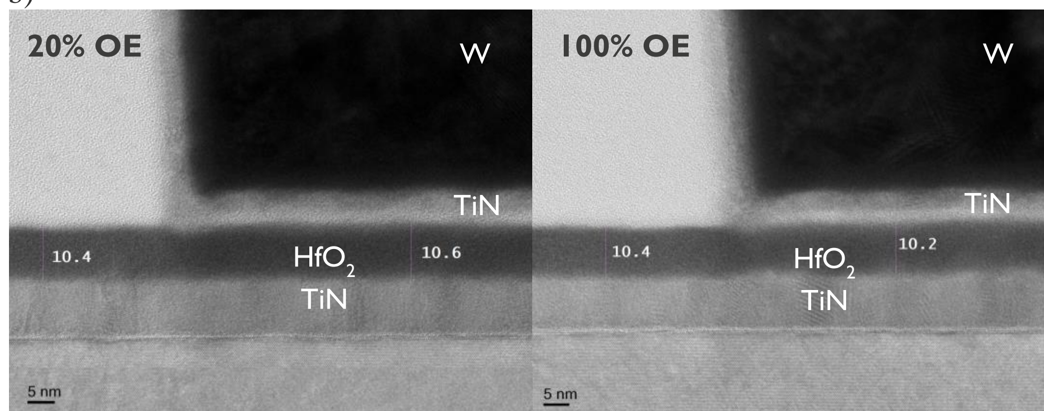
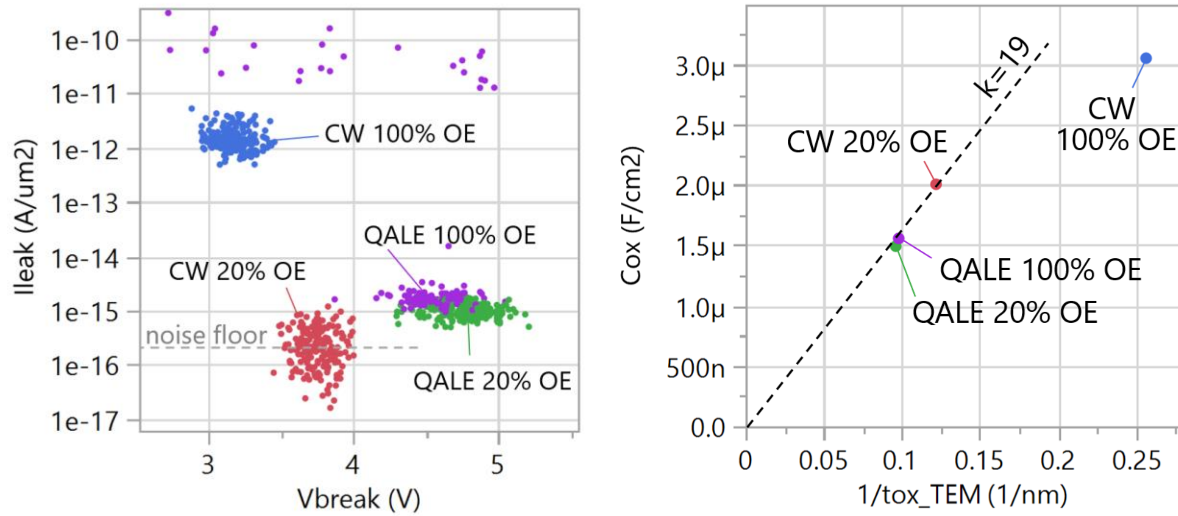


Figure 3. Current-voltage (I-V) and capacitance-voltage (C-V) measurements were performed on the 60x80um^2 MIMCAP devices to extract the DC leakage current (I_{leak}), the hard breakdown voltage (V_{break}), and the oxide capacitance (C_{ox}).



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